



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application of
Applicants : Rhodes et. al
Serial No. : 09/008,531
Filed : January 16, 1998
Title : METHOD OF MAKING A SEMICONDUCTOR DEVICE HAVING
IMPROVED CONTACTS TO A THIN CONDUCTIVE LAYER
Docket No. : MIO0012V2
Examiner : EATON
Art Unit : 2823

Box CPA
Assistant Commissioner for Patents
Washington, DC 20231

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Sir:

PRELIMINARY AMENDMENT

Please enter this amendment prior to any Office Actions. Reconsideration of the present application is respectfully requested in light of the remarks and amendments below.

IN THE CLAIMS

Please add new claims 31-39.

31. (New) A process for making a semiconductor device comprising:
forming a layer of conductive material having a topography that includes a substantially vertical component;
forming a contact disposed adjacent to and contacting said vertical component;
and
forming a structure having an opening therein under said conductive layer and filling said opening with said conductive material to form said vertical component.

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